

UNISONIC TECHNOLOGIES CO., LTD

UH11K

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

SOT-363

# DUAL BIAS RESISTOR TRANSISTORS

### DESCRIPTION

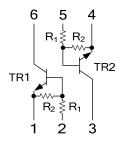
The UTC **UH11K** is a dual bias resistor transistors, it uses UTC's advanced technology to provide customers with saving board space, reducing component count, etc.

The UTC **UH11K** is suitable for low power surface mount applications, etc.

### FEATURES

- \* Reducing component count
- \* Saving board space

#### EQUIVALENT CIRCUIT

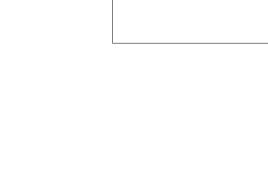


#### ORDERING INFORMATION

Ordering Number		Package		Pin Assignment					Deaking	
				2	3	4	5	6	Packing	
UH11KG-AL6-R	SOT-363		E1	B1	C2	E2	B2	C1	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source										
UH11KG-AL6-R (1)Packing Type (2)Package Type (3)Green Package		<ul><li>(1) R: Tape Reel</li><li>(2) AL6: SOT-363</li><li>(3) G: Halogen Free and Lead Free</li></ul>								

#### MARKING





## Preliminary NPN EPITAXIAL SILICON TRANSISTOR

#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Collector Current	lc	100	mA
Power Dissipation	PD	150	mW
Junction Temperature	TJ	-55~+150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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#### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =10μΑ, I <sub>E</sub> =0	50			V			
Collector-Emitter Breakdown Voltage (Note 1)	BV <sub>CEO</sub>	I <sub>C</sub> =2.0mA, I <sub>B</sub> =0	50			V			
Collector-Base Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0			100	nA			
Collector-Emitter Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =50V, I <sub>B</sub> =0			500	nA			
Emitter-Base Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =6.0V, I <sub>C</sub> =0			0.5	mA			
ON CHARACTERISTICS (Note 2)									
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =5.0mA	35	60					
Output Voltage (on)	Vol	$V_{CC}$ =5.0V, $V_{B}$ =2.5V, $R_{L}$ =1.0 k $\Omega$			0.2	V			
ON CHARACTERISTICS (Note 2)									
Input Resistor	R <sub>1</sub>		7.0	10	13	kΩ			
Resistor Ratio	$R_1/R_2$		0.8	1.0	1.2	kΩ			

Notes: 1. Pulse Test: Pulse Width<300µs, Duty Cycle<2.0%

2. Pulse Test: Pulse Width<300ms, Duty Cycle<2.0%



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